

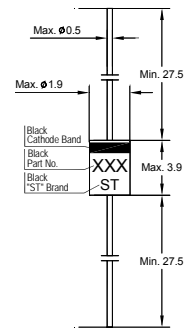
1SS171

Silicon Epitaxial Planar Switching Diode

for high speed switching circuits

Features

- High switching speed
- Small terminal capacitance
- Large forward current



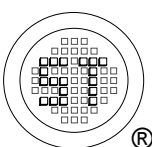
Glass Case DO-35
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	80	V
Reverse Voltage	V_R	80	V
Average Forward Current	$I_{F(AV)}$	200	mA
Repetitive Peak Forward Current	I_{FRM}	600	mA
Non-Repetitive Peak Forward Surge Current (at $t = 1\text{ s}$)	I_{FSM}	1	A
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 175	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25\text{ }^\circ\text{C}$

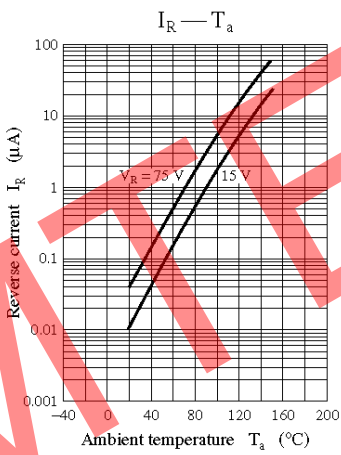
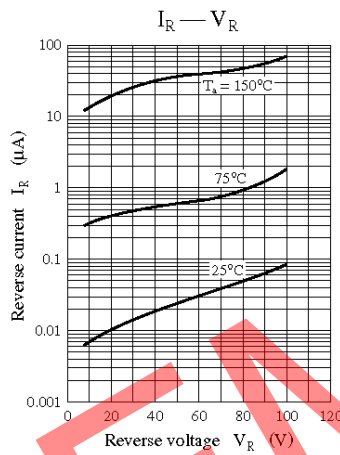
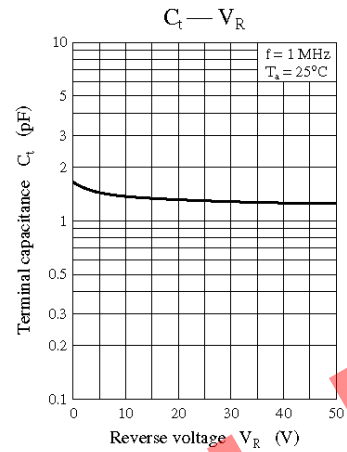
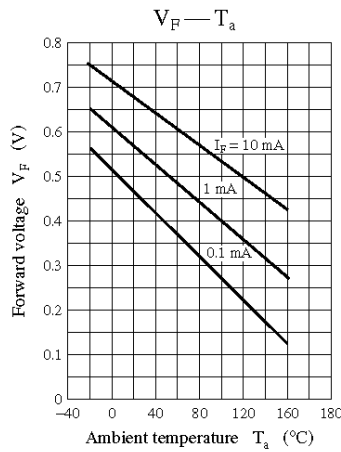
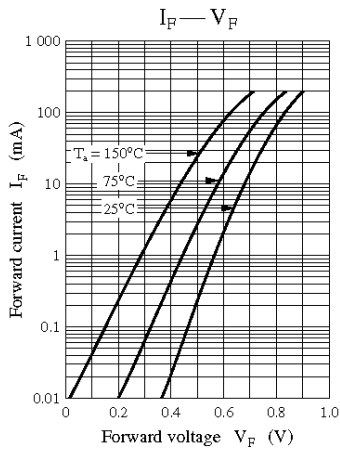
Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	V_F	1.1	V
Reverse Current at $V_R = 15\text{ V}$ at $V_R = 75\text{ V}$	I_R	50 500	nA
Terminal Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_T	4	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$, $I_{rr} = 0.1 I_R$, $R_L = 100\ \Omega$	t_{rr}	20	ns



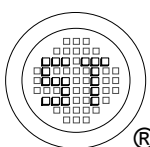
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Dated : 15/06/2009



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